

Tentative Data sheet

1L10ES-A_CP2

Active area: 10,0 x 2,0 mm²

Chip area: 12,2 x 3,0 mm²

Characteristics	Min.	Typ.	Max.	Unit
Position non-linearity		0,05	0,2	% (±)
Detector resistance	40	50	80	kΩ
Leakage current		8	50	nA
Noise current		0,4	1,0	pA/√Hz
Responsivity		3		A/W
Capacitance		15	20	pF
Rise time (10%-90%)		2	4	μs
Bias voltage (reverse)	5	15	20	V
Thermal drift		20	100	ppm/°C

Maximum ratings

Reverse voltage	30	V
Operating temperature	70	°C
Storage temperature	100	°C

Test conditions: Room temperature 23 °C, bias voltage 15V, light source wavelength 940 nm. Position non-linearity and thermal drift are valid within 80 % of the detector length.

Package: 14-pin DIL package, 19,6 x 7,6 mm², with protective window.

